

AMENDMENTS TO THE CLAIMS:

Claim 1. (Currently amended) A method of manufacturing a semiconductor device,
which comprises ~~the steps of:~~

depositing, on a basic substance surface with a difference in level, a first film through
an anisotropic growth;

forming, through an isotropic growth, a second film, having a polishing rate
equivalent to or less than a polishing rate of said first film, to reinforce a projection formed on
said first film; and

polishing said first film and said second film using a ceria slurry.

Claim 2. (Currently amended) The ~~A~~ method of manufacturing a semiconductor device
according to Claim 1, wherein said difference in level comprises ~~is formed of~~ a trench.

Claim 3. (Currently amended) The ~~A~~ method of manufacturing a semiconductor device
according to Claim 1, wherein said difference in level comprises ~~is formed of~~ an
interconnection.

Claim 4. (Currently amended) The ~~A~~ method of manufacturing a semiconductor device
according to claim ~~Claims~~ 1, wherein a stopper film which is to act as a polishing stopper,
having a polishing rate less than a polishing rate of said first film, is formed on an upper level
section constituting said difference in level.

Claim 5. (Currently amended) The ~~A~~ method of manufacturing a semiconductor device

according to Claim 4, wherein said first film and said second film ~~are~~ both comprise oxide films and said stopper film comprises ~~is~~ a nitride film.

Claim 6. (Currently amended) ~~The~~ A method of manufacturing a semiconductor device according to Claim 1, wherein said first film comprises ~~is~~ a film formed by ~~a~~ the high density plasma ~~CVD~~ (Chemical Vapor Deposition) method.

Claim 7. (Currently amended) ~~The~~ A method of manufacturing a semiconductor device according to Claim 1, wherein said second film comprises ~~is~~ a film formed by one of ~~an~~ the atmospheric chemical vapor deposition ~~CVD~~ method, ~~a~~ the low pressure chemical vapor deposition ~~CVD~~ method, and ~~a~~ the plasma chemical vapor deposition ~~CVD~~ method.

Claims 8-21. (Canceled).

Claim 22. (New) The method of claim 1, further comprising polishing said first film and said second film using a slurry whose grains do not make aggregation before said polishing said first film and said second film using said ceria slurry.

Claim 23. (New) The method of claim 1, wherein the polishing rate of the first film and the second film are within twenty percent of each other.

Claim 24. (New) The method of claim 1, wherein a thickness of said second film is not less than about 100 nm.

Claim 25. (New) The method of claim 1, wherein a thickness of said second film is not greater than about 400 nm.

Claim 26. (New) A method of manufacturing a semiconductor device, the method comprising:

anisotropically growing a first film on a substance surface having differences in level;
isotropically growing a second film which reinforces a projection on said first film,
wherein said second film has a polishing rate that is equal to or less than a polishing rate of said first film; and
polishing said first film and said second film using a ceria slurry.

Claim 27. (New) The method of claim 26, wherein said difference in level comprises a trench.

Claim 28. (New) The method of claim 26, wherein said difference in level comprises an interconnection.

Claim 29. (New) The method of claim 1, further comprising forming a stopper film on an upper level section constituting said difference in level.

Claim 30. (New) The method of claim 29, wherein said first film and said second film both comprise oxide films and said stopper film comprises a nitride film.

Claim 31. (New) The method of claim 26, wherein said anisotropically growing of said first film comprises a high density plasma chemical vapor deposition method.

Claim 32. (New) The method of claim 1, wherein said isotropically growing of said second film comprises forming said second film by at least one of an atmospheric chemical vapor deposition method, a low pressure chemical vapor deposition method, and a plasma chemical vapor deposition method.